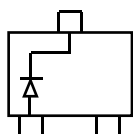


Plastic-Encapsulate Diodes

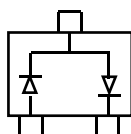
SCHOTTKY BARRIER DIODE

FEATURES

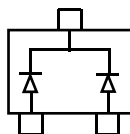
- Low Turn-on Voltage
- Fast Switching



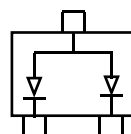
BAS70T Marking: 7C



BAS70-04T Marking: 7D

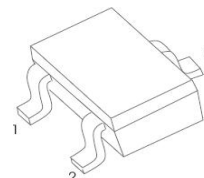


BAS70-05T Marking: 7E

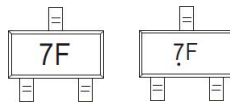


BAS70-06T Marking: 7F

SOT-523



MARKING:

BAS70T	BAS70-04T	BAS70-05T	BAS70-06T
			

Maximum Ratings @Ta=25°C

Parameter	Symbol	Limit	Unit
Peak Repetitive Peak Reverse Voltage	V_{RRM}	70	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
Forward Continuous Current	I_{FM}	70	mA
Non-Repetitive Peak Forward Surge Current @ t = 8.3ms	I_{FSM}	100	mA
Power Dissipation	P_D	150	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	667	°C/W
Junction temperature	T_J	125	°C
Storage Temperature	T_{STG}	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=10\mu A$	70		V
Reverse voltage leakage current	I_R	$V_R=50V$		100	nA
Forward voltage	V_F	$I_F=1mA$ $I_F=15mA$		410 1000	mV
Diode capacitance	C_D	$V_R=0, f=1MHz$		2	pF
Reverse recovery time	t_{rr}	$I_F=I_R=10mA, I_{rr}=0.1I_R$ $R_L=100\Omega$		5	ns

Typical Characteristics

